

## CDBD2SC6650-G

**Reverse Voltage: 650 V**

**Forward Current: 6 A**

**RoHS Device**



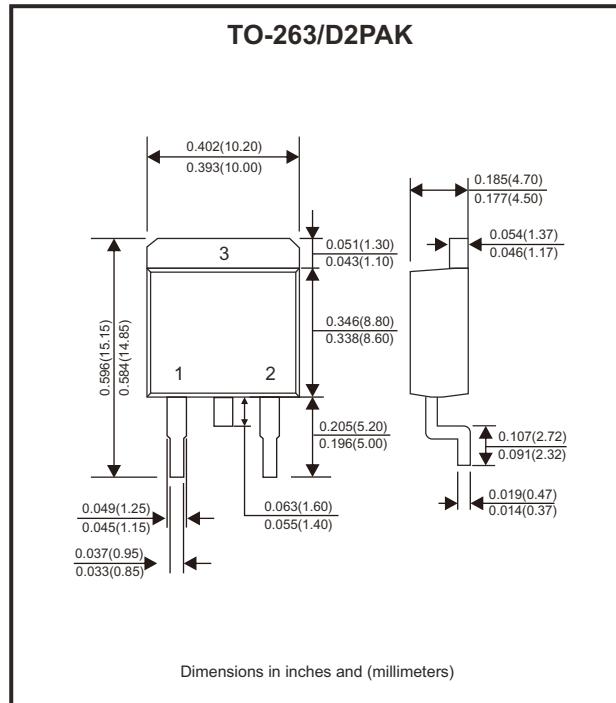
### Features

- Rated to 650V at 6 Amps
- Short recovery time.
- High speed switching possible.
- High frequency operation.
- High temperature operation.
- Temperature independent switching behaviour.
- Positive temperature coefficient on VF.

### Mechanical data

- Case: TO-263/D2PAK, molded plastic.
- Terminals: Solderable per MIL-STD-750, method 2026.

### Circuit Diagram



### Maximum Ratings (at $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Conditions	Symbol	Value	Unit
Repetitive peak reverse voltage		$V_{RRM}$	650	V
Surge peak reverse voltage		$V_{RSM}$	650	V
DC blocking voltage		$V_{DC}$	650	V
Continuous forward current	$T_c = 150^\circ\text{C}$	$I_F$	6	A
Repetitive peak forward surge current	$T_c = 25^\circ\text{C}$ , $t_p = 10\text{ms}$ Half sine wave, $D = 0.3$	$I_{FRM}$	30	A
Non-repetitive peak forward surge current	$T_c = 25^\circ\text{C}$ , $t_p = 10\text{ms}$ Half sine wave	$I_{FSM}$	60	A
Power dissipation	$T_c = 25^\circ\text{C}$	$P_{TOT}$	85.8	W
	$T_c = 110^\circ\text{C}$		37.2	
Typical thermal resistance	Junction to case	$R_{\theta JC}$	1.748	°C/W
Operating junction temperature range		$T_J$	-55 ~ +175	°C
Storage temperature range		$T_{STG}$	-55 ~ +175	°C

# Silicon Carbide Power Schottky Diode

**Comchip**  
SMD Diode Specialist

## Electrical Characteristics (at $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 6\text{A}, T_J = 25^\circ\text{C}$	$V_F$		1.44	1.7	V
	$I_F = 6\text{A}, T_J = 175^\circ\text{C}$			1.73	2.5	
Reverse current	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	$I_R$		10	100	$\mu\text{A}$
	$V_R = 650\text{V}, T_J = 175^\circ\text{C}$			15	200	
Total capacitive charge	$V_R = 400\text{V}, T_J = 150^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V) dV$	$Q_C$		23		nC
Total capacitance	$V_R = 0\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$	$C$		424	434	$\text{pF}$
	$V_R = 200\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$			44	45	
	$V_R = 400\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$			42.5	43	

## Rating and Characteristics Curves (CDBD2SC6650-G)

Fig.1 - Forward Characteristics

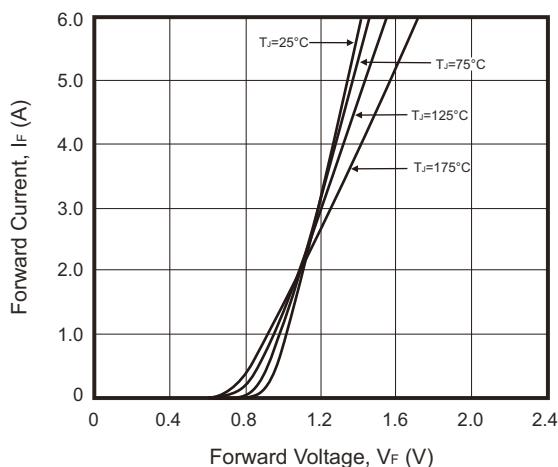


Fig.2 - Reverse Characteristics

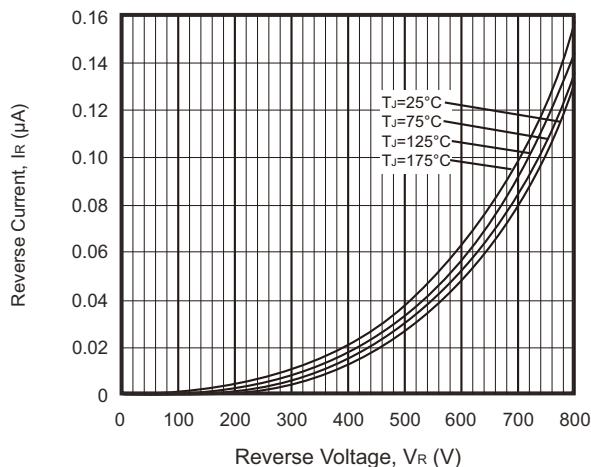


Fig.3 - Current Derating

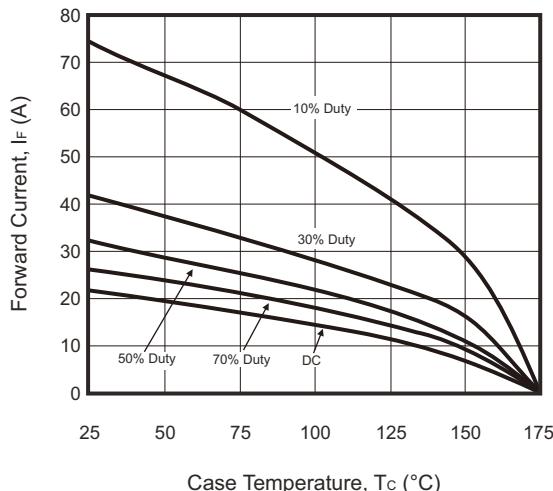
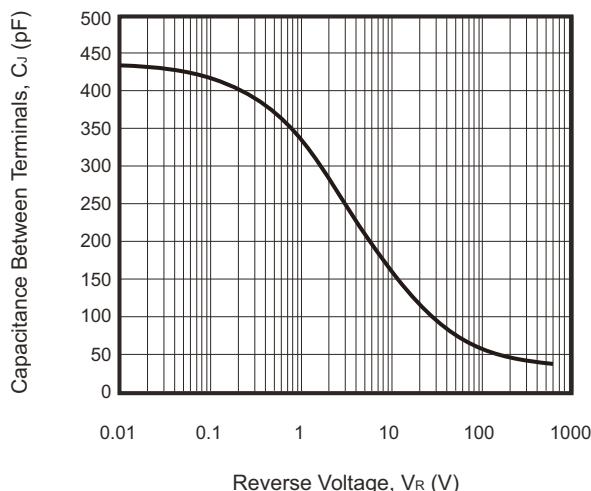
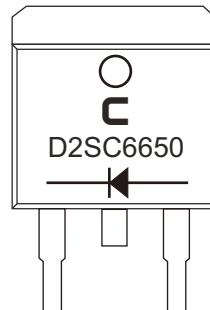


Fig.4 - Capacitance Characteristics

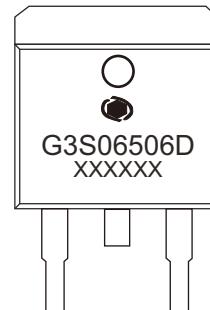


## Marking Code

Part Number	Marking Code	
CDBD2SC6650-G	D2SC6650	G3S06506D



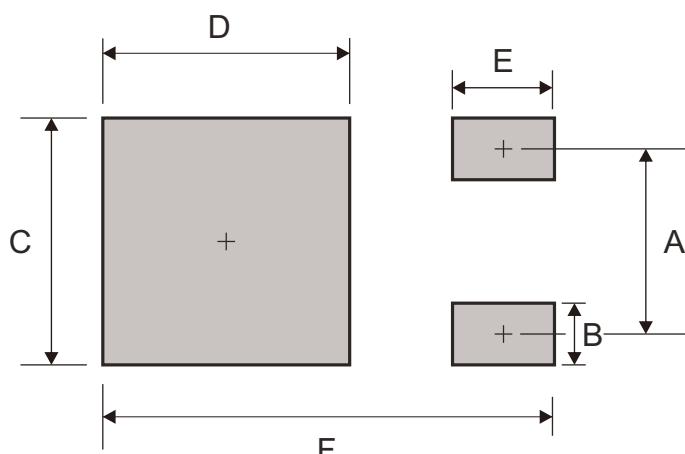
**C** = Comchip Logo



xxxxxx = Control code  
(x from 6 to 11)

## Suggested P.C.B. PAD Layout

SIZE	TO-263 / D2PAK	
	(mm)	(inch)
A	5.08	0.200
B	1.10	0.043
C	10.80	0.425
D	8.30	0.327
E	3.50	0.138
F	16.90	0.665



## Standard Packaging

Case Type	TUBE PACK	
	TUBE ( pcs )	BOX ( pcs )
TO-263/D2PAK	50	1,000